



SRI VASAVI INSTITUTE OF ENGINEERING & TECHNOLOGY
Department of Electronics and Communication Engineering

Differentiation

COURSE :VLSID (C322)
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Semester: II

Class: III B.Tech ECE A&B

sheet Resistance R_s of MOS Layers for different technologies ($5\mu m$, $2\mu m$, $1.2\mu m$)

Layer	R_s ohm per square		
	$5\mu m$	Orbit	Orbit $1.2\mu m$
Metal	0.03	0.04	0.04
Diffusion (or active)**	10→50	20→45	20→45
Silicide	2→4	—	—
Polysilicon	15→100	15→30	15→30
n-transistor channel	$10^{4\uparrow}$	$2 \times 10^{4\uparrow}$	$2 \times 10^{4\uparrow}$
p-transistor channel	$2.5 \times 10^{4\uparrow}$	$4.5 \times 10^{4\uparrow}$	$4.5 \times 10^{4\uparrow}$

area capacitance values for MOS circuits

Capacitance	Value in $pF \times 10^{-4}/\mu m^2$ (Relative values in brackets)		
	$5\mu m$	$2\mu m$	$1.2\mu m$
Gate to channel	4 (1.0)	8 (1.0)	16 (1.0)
Diffusion (active)	1 (0.25)	1.75 (0.22)	3.75 (0.23)
Polysilicon* to substrate	0.4 (0.1)	0.6 (0.075)	0.6 (0.031)
Metal 1 to substrate	0.3 (0.075)	0.33 (0.04)	0.33 (0.02)
Metal 2 to substrate	0.2 (0.05)	0.17 (0.02)	0.17 (0.01)
Metal 2 to metal 1	0.4 (0.1)	0.5 (0.06)	0.5 (0.03)
Metal 2 to polysilicon	0.3 (0.075)	0.3 (0.038)	0.3 (0.011)

- **For $5\mu m$ MOS circuits**

Area/standard square = $5\mu m \times 5\mu m = 25\mu m^2$ (minimum transistor size)

Capacitance value = $4 \times 10^{-4} pF/\mu m^2$ (from table 3.2)

Thus, standard value $\square C_g = 25\mu m^2 \times 4 \times 10^{-4} pF/\mu m^2 = 0.01 pF$

- **For $2\mu m$ MOS circuits**

Area/standard square = $2\mu m \times 2\mu m = 4\mu m^2$

Capacitance value = $8 \times 10^{-4} pF/\mu m^2$

Thus, standard value $\square C_g = 4\mu m^2 \times 8 \times 10^{-4} pF/\mu m^2 = 0.01 pF$

- **For $1.2\mu m$ MOS circuits**

Area/standard square = $1.2\mu m \times 1.2\mu m = 1.44\mu m^2$

Capacitance value = $16 \times 10^{-4} pF/\mu m^2$

Thus, standard value $\square C_g = 1.44\mu m^2 \times 16 \times 10^{-4} pF/\mu m^2 = 0.0023 pF$

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